

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2002-151473
 (43)Date of publication of application : 24.05.2002

(51)Int.Cl.

H01L 21/3065
 B01J 19/08
 C23C 16/44
 H05H 1/46

(21)Application number : 2000-345008

(71)Applicant : TOKYO ELECTRON LTD

(22)Date of filing : 13.11.2000

(72)Inventor : TOMOYOSHI TSUTOMU
 KOIZUMI KATSUYUKI

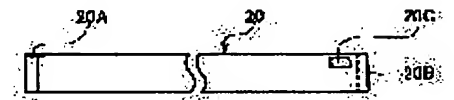
(54) PLASMA PROCESSING APPARATUS AND ITS ASSEMBLING METHOD

(57)Abstract:

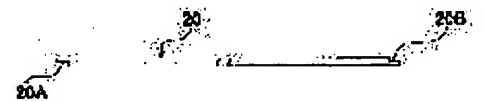
PROBLEM TO BE SOLVED: To overcome the problem of a prior art such that plasma processing is affected adversely when the surface of a shield member 9 is cut off partially by plasma and the surface treatment film is eliminated and, since a decision is made that the life of the shield member 9 has expired even when a limited part thereof is cut off, the shield member 9 must be replaced and a high cost is imposed for replacing the shield member 9.

SOLUTION: The plasma processing apparatus 10 comprises a lower electrode 12 for supporting a wafer W in a chamber 11, a member 19 for shielding the inner circumferential surface of the chamber 11 from plasma for processing the wafer W supported by the lower electrode 12, and a baffle plate 18 disposed in a gap between the shielding member 19 and the lower electrode 12 in order to discharge gas in the chamber 11 while diffusing, wherein a resin plate 20 is fixed replaceably to the inner circumferential surface of the shielding member 19, and the resin plate 20 is imparted with a compressive stress in the circumferential direction.

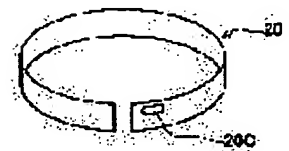
(a)



(b)



(c)



(d)

